

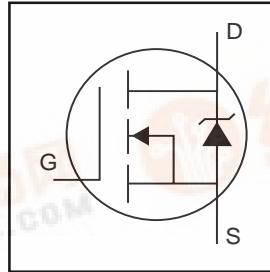
# International Rectifier

PRELIMINARY

# IRL3502

HEXFET<sup>®</sup> Power MOSFET

- Advanced Process Technology
- Optimized for 4.5V-7.0V Gate Drive
- Ideal for CPU Core DC-DC Converters
- Fast Switching

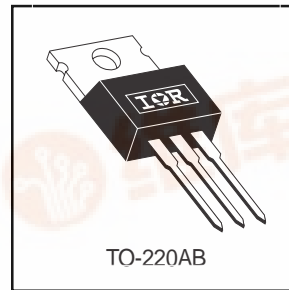


$V_{DS} = 20V$
$R_{DS(on)} = 0.007\Omega$
$I_D = 110A$ ⑤

## Description

These HEXFET Power MOSFETs were designed specifically to meet the demands of CPU core DC-DC converters. Advanced processing techniques combined with an optimized gate oxide design results in a die sized specifically to offer maximum efficiency at minimum cost.

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 watts. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.

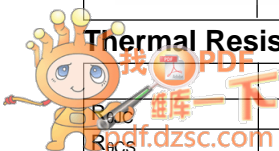


## Absolute Maximum Ratings

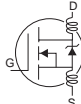
	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 5.0V$	110⑤	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 5.0V$	67	
$I_{DM}$	Pulsed Drain Current ①	420	
$P_D @ T_C = 25^\circ C$	Power Dissipation	140	W
	Linear Derating Factor	1.1	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 10$	V
$V_{GSM}$	Gate-to-Source Voltage (Start Up Transient, $t_p = 100\mu s$ )	14	V
$E_{AS}$	Single Pulse Avalanche Energy②	390	mJ
$I_{AR}$	Avalanche Current①	64	A
$E_{AR}$	Repetitive Avalanche Energy①	14	mJ
$dv/dt$	Peak Diode Recovery $dv/dt$ ③	5.0	V/ns
$T_J$	Operating Junction and Storage Temperature Range	-55 to + 150	°C
$T_{STG}$			
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

## Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{JC}$	Junction-to-Case	—	0.89	°C/W
$R_{BCS}$	Case-to-Sink, Flat, Greased Surface	0.50	—	
$R_{JA}$	Junction-to-Ambient	—	62	



## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	20	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.019	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}$ , $I_D = 1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.008	$\Omega$	$V_{GS} = 4.5V, I_D = 64A$ ④
		—	—	0.007		$V_{GS} = 7.0V, I_D = 64A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	0.70	—	—	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$g_{fs}$	Forward Transconductance	77	—	—	S	$V_{DS} = 10V, I_D = 64A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	25	$\mu A$	$V_{DS} = 20V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 10V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = -10V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = 10V$
$Q_g$	Total Gate Charge	—	—	110	nC	$I_D = 64A$
$Q_{gs}$	Gate-to-Source Charge	—	—	27		$V_{DS} = 16V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	—	39		$V_{GS} = 4.5V$ , See Fig. 6 ④
$t_{d(on)}$	Turn-On Delay Time	—	10	—	ns	$V_{DD} = 10V$
$t_r$	Rise Time	—	140	—		$I_D = 64A$
$t_{d(off)}$	Turn-Off Delay Time	—	96	—		$R_G = 3.8\Omega, V_{GS} = 4.5V$
$t_f$	Fall Time	—	130	—		$R_D = 0.15\Omega$ , ④
$L_D$	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
$L_S$	Internal Source Inductance	—	7.5	—		
$C_{iss}$	Input Capacitance	—	4700	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	1900	—		$V_{DS} = 15V$
$C_{rss}$	Reverse Transfer Capacitance	—	640	—		$f = 1.0MHz$ , See Fig. 5

## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	110	A	MOSFET symbol showing the integral reverse p-n junction diode.
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	420		
$V_{SD}$	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 64A, V_{GS} = 0V$ ④
$t_{rr}$	Reverse Recovery Time	—	87	130	ns	$T_J = 25^\circ\text{C}, I_F = 64A$
$Q_{rr}$	Reverse Recovery Charge	—	200	310	nC	$di/dt = 100A/\mu s$ ④
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$ )				

### Notes:

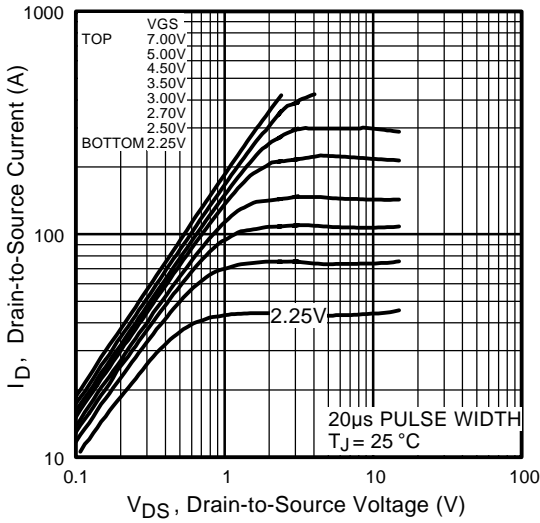
① Repetitive rating; pulse width limited by max. junction temperature.

② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 190\mu H$   
 $R_G = 25\Omega, I_{AS} = 64A$ .

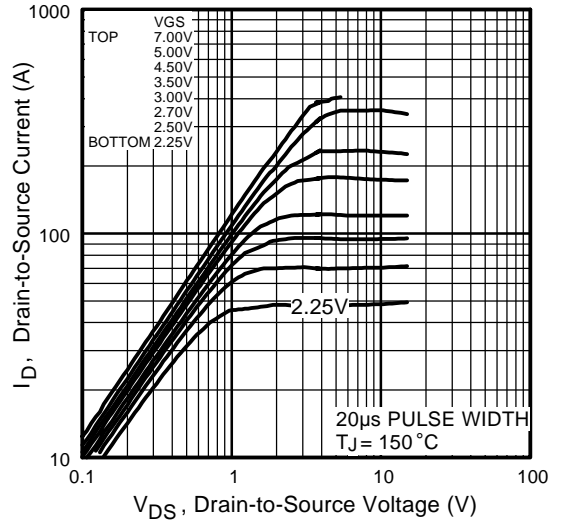
③  $I_{SD} \leq 64A, di/dt \leq 86A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 150^\circ\text{C}$

④ Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$ .

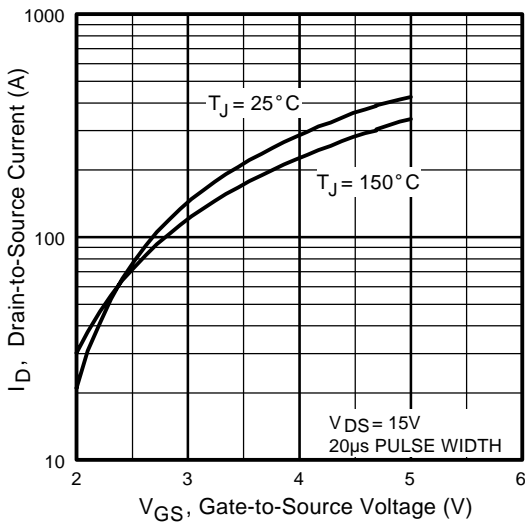
⑤ Calculated continuous current based on maximum allowable junction temperature; for recommended current-handling of the package refer to Design Tip # 93-4



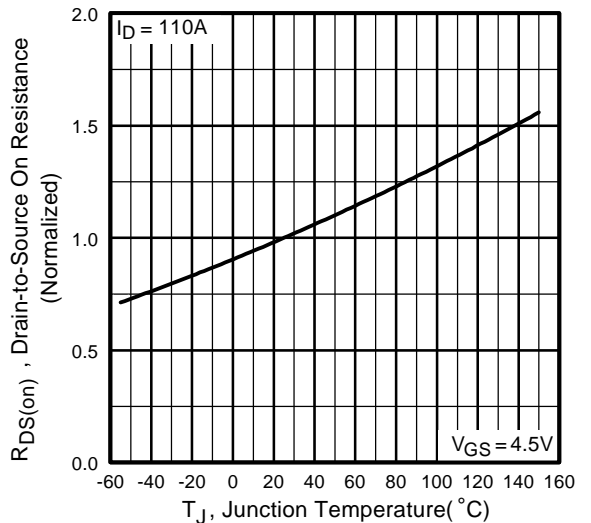
**Fig 1.** Typical Output Characteristics



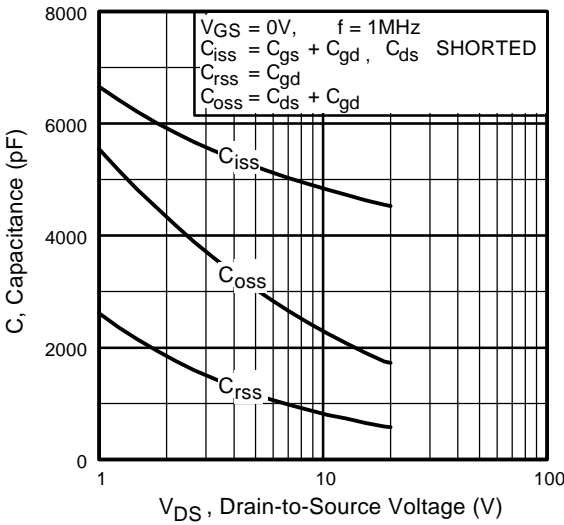
**Fig 2.** Typical Output Characteristics



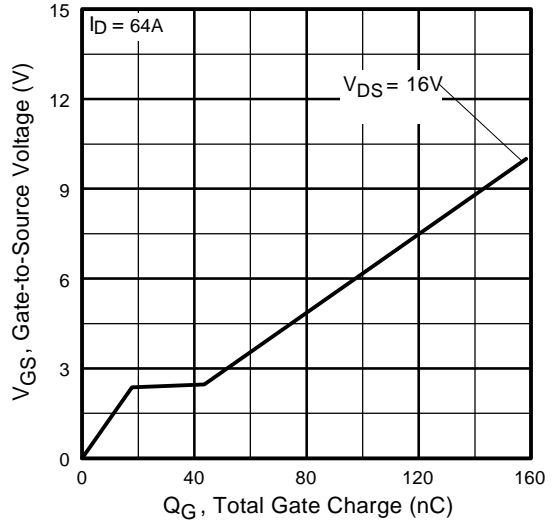
**Fig 3.** Typical Transfer Characteristics



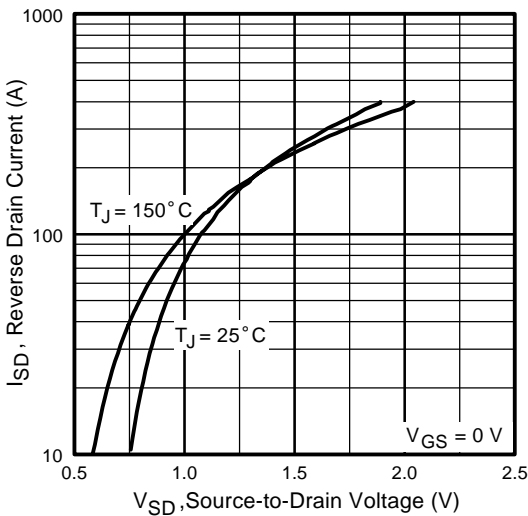
**Fig 4.** Normalized On-Resistance Vs. Temperature



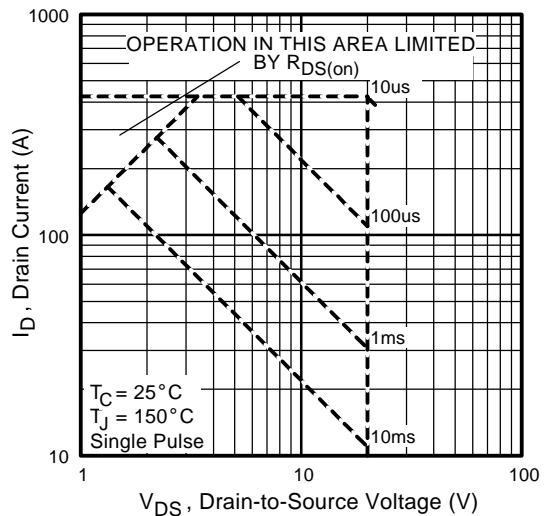
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



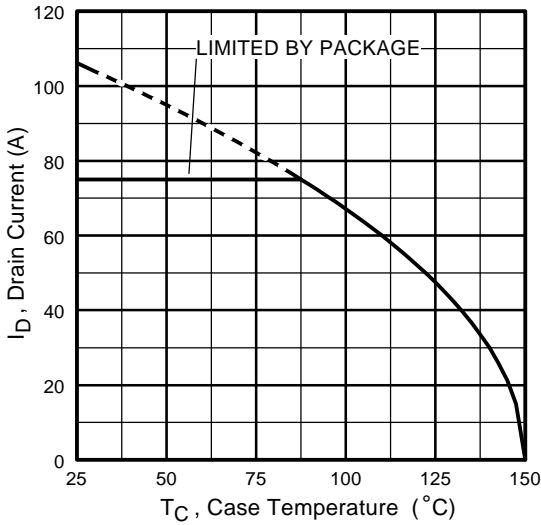
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



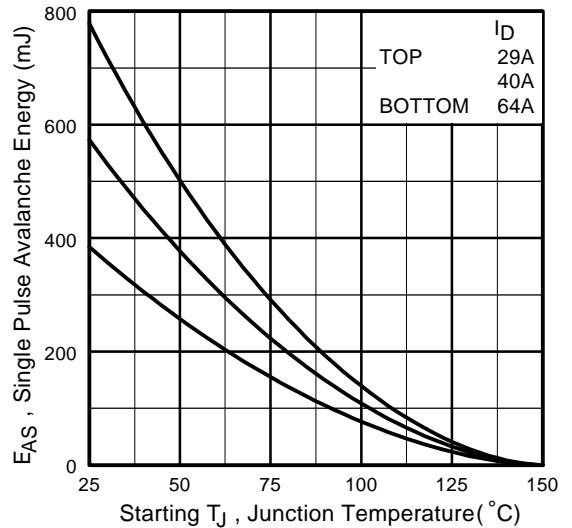
**Fig 7.** Typical Source-Drain Diode Forward Voltage



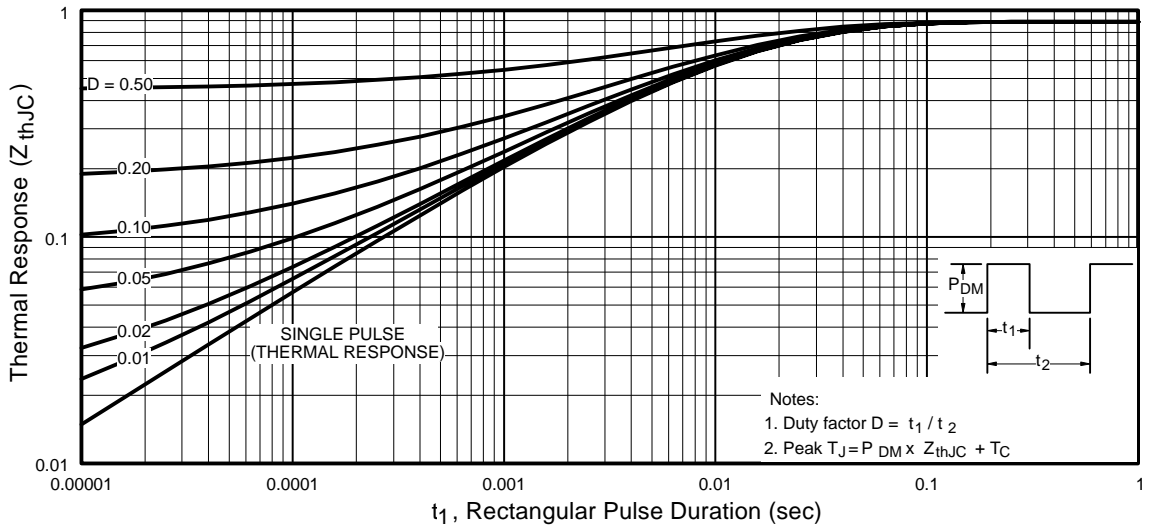
**Fig 8.** Maximum Safe Operating Area



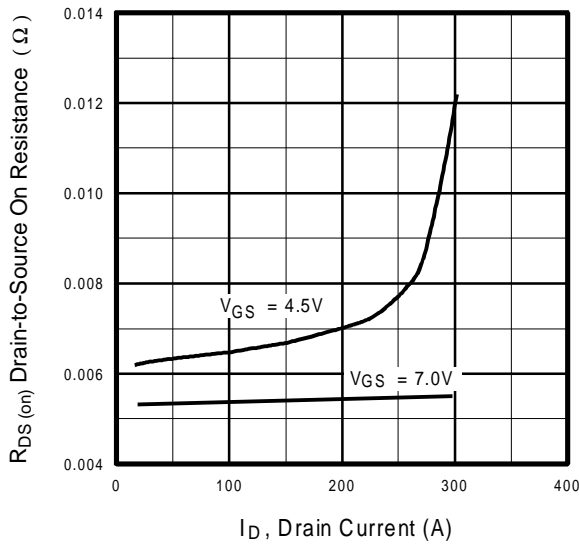
**Fig 9.** Maximum Drain Current Vs. Case Temperature



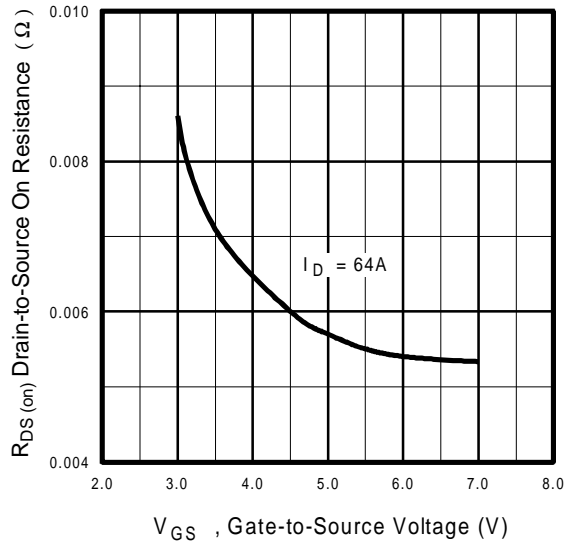
**Fig 10.** Maximum Avalanche Energy Vs. Drain Current



**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case



**Fig 12.** On-Resistance Vs. Drain Current

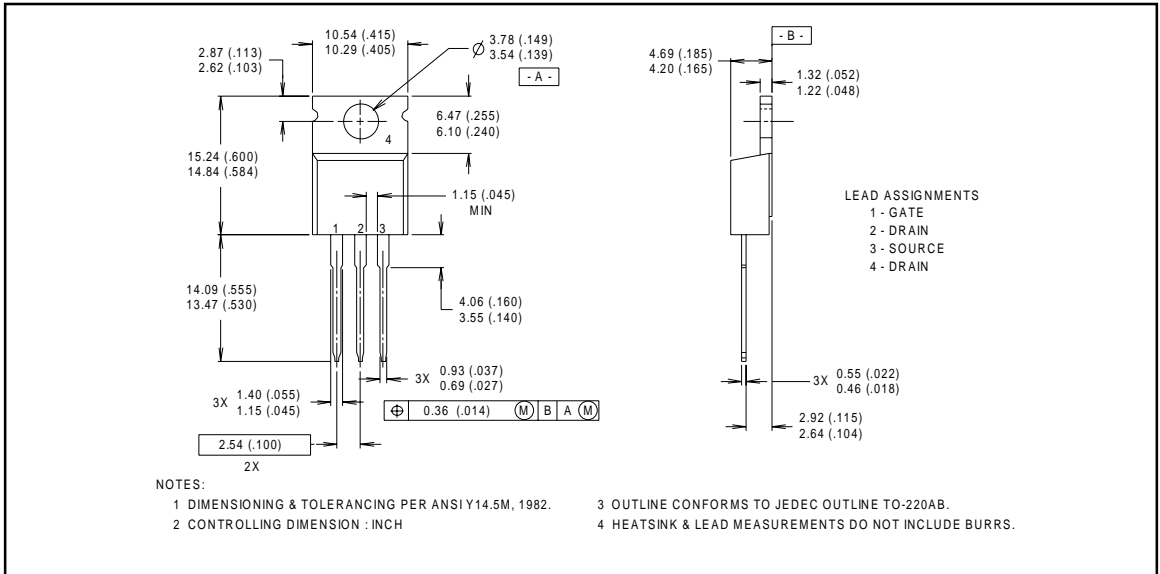


**Fig 13.** On-Resistance Vs. Gate Voltage

**Package Outline**

**TO-220AB Outline**

Dimensions are shown in millimeters (inches)



**Part Marking Information**

**TO-220AB**

